IN THE CLAIMS:

Please cancel claims 2 and 10, and amend the claims as follows:

1. (Currently Amended) A method for processing a substrate in a processing chamber, comprising:

forming ~~a conductive material~~ an aluminum-containing layer on a surface of the substrate;

depositing an amorphous carbon layer on the ~~conductive material~~ aluminum-containing layer by a method comprising:

introducing into the processing chamber one or more hydrocarbon compounds having the general formula C_xH_y, wherein x has a range of 2 to 4 and y has a range of 2 to 10; and

generating a plasma of the one or more hydrocarbon compounds by applying power from a dual-frequency RF source;

etching the amorphous carbon layer to form a patterned amorphous carbon layer; and

etching feature definitions in the ~~conductive material~~ aluminum-containing layer corresponding to the patterned amorphous carbon layer.

2. (Canceled)

3. (Previously Presented) The method of claim 6, wherein the first frequency is provided at a power between 200 watts and 800 watts and the second frequency is provided at a power between about 1 watt and about 200 watts.

4. (Previously Presented) The method of claim 1, wherein the one or more hydrocarbon compounds are selected from the group consisting of propylene (C_3H_6), propyne (C_3H_4), propane (C_3H_8), butane (C_4H_{10}), butylene (C_4H_8), butadiene (C_4H_6), acetylene (C_2H_2), and combinations thereof.

5. (Previously Presented) The method of claim 1, further comprising introducing an inert gas with the one or more hydrocarbons into the processing chamber.

6. (Previously Presented) The method of claim 1, wherein the dual-frequency RF source comprises providing a first frequency between about 10 MHz and about 30 MHz and a second frequency between about 100 KHz and about 500 KHz.

7. (Original) The method of claim 1, wherein the etch selectivity of amorphous carbon to the conductive material is between about 1:3 and about 1:10.

8. (Original) The method of claim 1, wherein the amorphous carbon layer comprises an anti-reflective coating.

9. (Currently Amended) A method for processing a substrate in a chamber, comprising:

forming ~~a conductive material~~ an aluminum-containing layer on a surface of the substrate;

depositing an amorphous carbon hardmask on the ~~conductive material~~ aluminum-containing layer by a method comprising:

introducing into the processing chamber one or more hydrocarbon compounds having the general formula C_xH_y, wherein x has a range of 2 to 4 and y has a range of 2 to 10; and

generating a plasma of the one or more hydrocarbon compounds by applying power from a dual-frequency RF source;

depositing an anti-reflective coating on the amorphous carbon hardmask;

depositing a patterned resist material on the anti-reflective coating;

etching the anti-reflective coating and amorphous carbon hardmask to the ~~conductive material~~ aluminum-containing layer; and

etching feature definitions in the ~~conductive material~~ aluminum-containing layer.

10. (Canceled)

11. (Previously Presented) The method of claim 14, wherein the first frequency is provided at a power between 200 watts and 800 watts and the second frequency is provided at a power between about 1 watt and about 200 watts.

12. (Previously Presented) The method of claim 9, wherein the one or more hydrocarbon compounds are selected from the group consisting of propylene (C_3H_6), propyne (C_3H_4), propane (C_3H_8), butane (C_4H_{10}), butylene (C_4H_8), butadiene (C_4H_6), acetylene (C_2H_2), and combinations thereof.

13. (Previously Presented) The method of claim 9, further comprising introducing an inert gas with the one or more hydrocarbons into the processing chamber.

14. (Previously Presented) The method of claim 9, wherein the dual-frequency RF source comprises providing a first frequency between about 10 MHz and about 30 MHz and a second frequency between about 100 KHz and about 500 KHz.

15. (Original) The method of claim 9, wherein the anti-reflective coating is a material selected from the group of silicon nitride, silicon carbide, carbon-doped silicon oxide, amorphous carbon, and combinations thereof.

16. (Previously Presented) The method of claim 9, further comprising depositing a barrier layer prior to depositing the conductive material layer.

17. (Previously Presented) The method of claim 9, further comprising removing the resist material prior to etching feature definitions in the conductive material layer.

18. (Original) The method of claim 9, wherein the etch selectivity of amorphous carbon to the conductive material is between about 1:3 and about 1:10.

19. (Previously Presented) A method for processing a substrate in a chamber, comprising:

forming an aluminum-containing layer on a surface of the substrate;

depositing an amorphous carbon hardmask on the aluminum-containing layer by a method comprising:

introducing into the processing chamber one or more hydrocarbon compounds having the general formula C_xH_y, wherein x has a range of 2 to 4 and y has a range of 2 to 10; and

generating a plasma of the one or more hydrocarbon compounds by applying power from a dual-frequency RF source;

depositing an anti-reflective coating on the amorphous carbon hardmask, wherein the anti-reflective coating is a material selected from the group of silicon nitride, silicon carbide, carbon-doped silicon oxide, amorphous carbon, and combinations thereof;

depositing a patterned resist material on the anti-reflective coating;

etching the anti-reflective coating and amorphous carbon hardmask to the aluminum-containing layer;

removing the resist material;

etching feature definitions in the aluminum-containing layer at an etch selectivity of amorphous carbon to the aluminum-containing between about 1:3 and about 1:10; and

removing the one or more amorphous carbon layers by exposing the one or more amorphous carbon layers to a plasma of a hydrogen-containing gas or an oxygen-containing gas.

20. (Previously Presented) The method of claim 19, wherein the one or more hydrocarbon compounds are selected from the group consisting of propylene (C_3H_6), propyne (C_3H_4), propane (C_3H_8), butane (C_4H_{10}), butylene (C_4H_8), butadiene (C_4H_6), acetylene e (C_2H_2), and combinations thereof.

21. (Original) The method of claim 19, further comprising introducing an inert gas with the one or more hydrocarbons into the processing chamber.

22. (Previously Presented) The method of claim 19, wherein the generating a plasma comprises applying power from a dual-frequency RF source comprises providing a first frequency between about 10 MHz and about 30 MHz at a power between 200 watts and 800 watts and a second frequency between about 100 KHz and about 500 KHz at a power between about 1 watt and about 200 watts.